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GaOCl monolayer: a novel wide-bandgap 2D material with hole-doping-induced ferromagnetism and multidirectional piezoelectricity

Shujuan Jiang,[a] Huabing Yin,[* b] and Guang-Ping Zheng [* a]

[a.] *Department of Mechanical Engineering, The Hong Kong Polytechnic University, Hung Hom, Kowloon, Hong Kong 999077, China.*

[b.] *Institute for Computational Materials Science, School of Physics and Electronics, Henan University, Kaifeng 475004, China.*

*E-mails: mmzheng@polyu.edu.hk (G.-P. Zheng); yhb@henu.edu.cn (H. Yin)

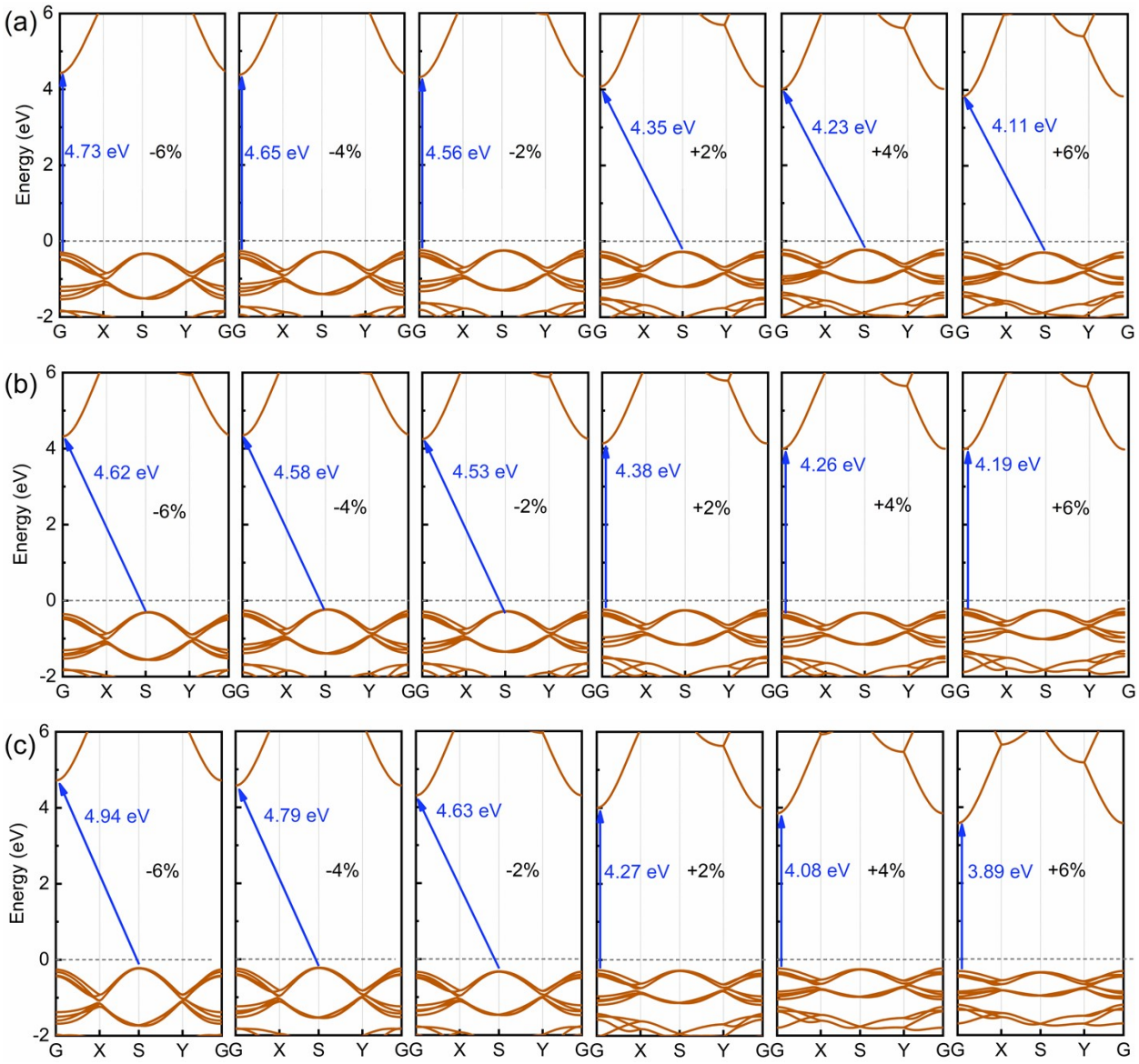

Figure S1. HSE06 band structures of GaOCl monolayer under the in-plane uniaxial strains varying from −6% to +6% along (a) *x*-, (b) *y*- and (c) *xy*-directions. The bandgaps are highlighted in blue. The Fermi level is at 0 eV.

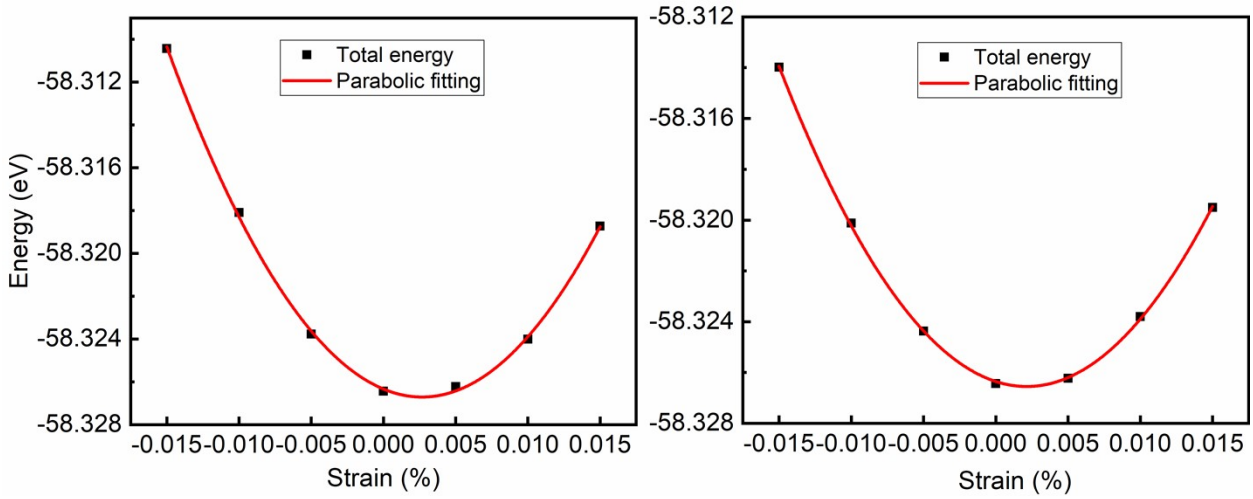

Figure S2. The total energy of GaOCl monolayer as a function of uniaxial strains applied along (a) x-direction, and (b) y-direction, respectively.